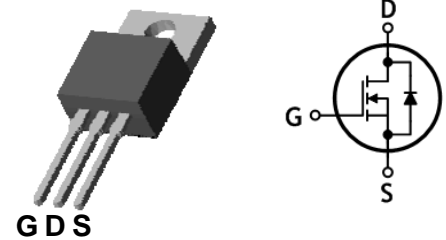


SWITCHING REGULATOR APPLICATION

Features

- Drain-Source breakdown voltage: $BV_{DSS} = 500V$
- Low gate charge: $Q_g = 46nC$ (Typ.)
- Low drain-source On resistance: $R_{DS(on)} = 0.3\Omega$ (Max.)
- 100% avalanche tested
- RoHS compliant device

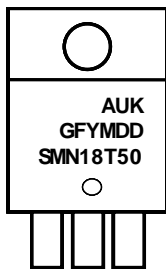


Ordering Information

Part Number	Marking	Package
SMN18T50P	SMN18T50	TO-220AB

TO-220AB

Marking Information



Column 1: Manufacturer
 Column 2: Production Information
 e.g.) GFYMDD
 -. G: Option Code (H: Halogen Free)
 -. F: Factory Management Code
 -. YMDD: Date Code (Year, Month, Date)
 Column 3: Device Code

Absolute maximum ratings ($T_c = 25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit	
Drain-source voltage	V_{DSS}	500	V	
Gate-source voltage	V_{GSS}	± 30	V	
Drain current (DC) *	I_D	$T_c = 25^\circ C$	18	A
		$T_c = 100^\circ C$	11.4	A
Drain current (Pulsed) *	I_{DM}	72	A	
Single pulsed avalanche energy ^(Note 2)	E_{AS}	954	mJ	
Repetitive avalanche current ^(Note 1)	I_{AR}	18	A	
Repetitive avalanche energy ^(Note 1)	E_{AR}	29	mJ	
Power dissipation	P_D	290	W	
Peak diode recovery dv/dt ^(Note 3)	dv/dt	4.5	V/ns	
Junction temperature	T_J	150	$^\circ C$	
Storage temperature range	T_{stg}	-55~150	$^\circ C$	

* Drain current limited by maximum junction temperature

Thermal Characteristics

Characteristic	Symbol	Rating	Unit
Thermal resistance, junction to case	$R_{th(j-c)}$	Max. 0.43	°C/W
Thermal resistance, junction to ambient	$R_{th(j-a)}$	Max. 62.5	

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0$	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2	-	4	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=500\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=400\text{V}, T_c=125^\circ\text{C}$	-	-	10	μA
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$	-	-	± 100	nA
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=9\text{A}$	-	0.25	0.3	Ω
Forward transfer conductance (Note 4)	g_{fs}	$V_{DS}=10\text{V}, I_D=9\text{A}$	-	11	-	S
Input capacitance	C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$	-	3405	4643	pF
Output capacitance	C_{oss}		-	283	386	
Reverse transfer capacitance	C_{rss}		-	10.6	17	
Turn-on delay time (Note 4,5)	$t_{d(on)}$	$V_{DD}=250\text{V}, I_D=18\text{A}, R_G=25\Omega$	-	78	-	ns
Rise time (Note 4,5)	t_r		-	72	-	
Turn-off delay time (Note 4,5)	$t_{d(off)}$		-	184	-	
Fall time (Note 4,5)	t_f		-	68	-	
Total gate charge (Note 4,5)	Q_g	$V_{DS}=400\text{V}, V_{GS}=10\text{V}, I_D=18\text{A}$	-	46	62	nC
Gate-source charge (Note 4,5)	Q_{gs}		-	14	-	
Gate-drain charge (Note 4,5)	Q_{gd}		-	8.5	-	

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	18	A
Source current (Pulsed)	I_{SM}		-	-	72	A
Forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_S=18\text{A}$	-	-	1.5	V
Reverse recovery time (Note 4,5)	t_{rr}	$I_S=18\text{A}, V_{GS}=0\text{V}, di_f/dt=100\text{A}/\mu\text{s}$	-	360	-	ns
Reverse recovery charge (Note 4,5)	Q_{rr}		-	4.1	-	μC

Note:

1. Repeated rating: Pulse width limited by safe operating area
2. $L=5.3\text{mH}, I_{AS}=18\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
3. $I_S \leq 18\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$
4. Pulse test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature typical characteristics

Electrical Characteristics Curve

Fig. 1 $I_D - V_{DS}$

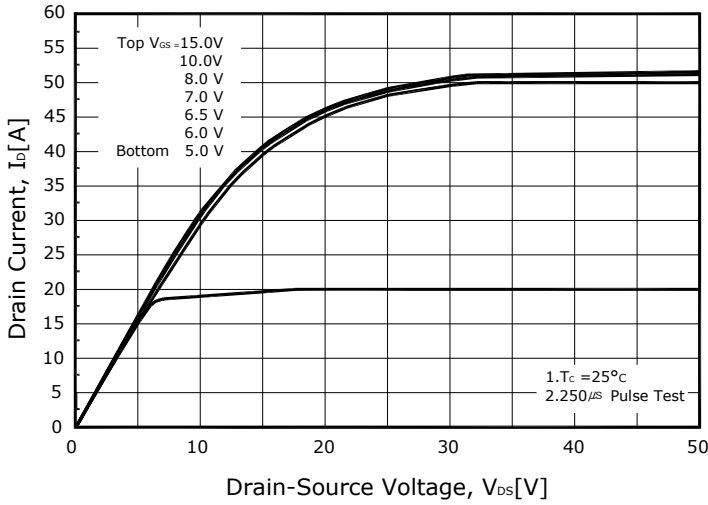


Fig. 2 $I_D - V_{GS}$

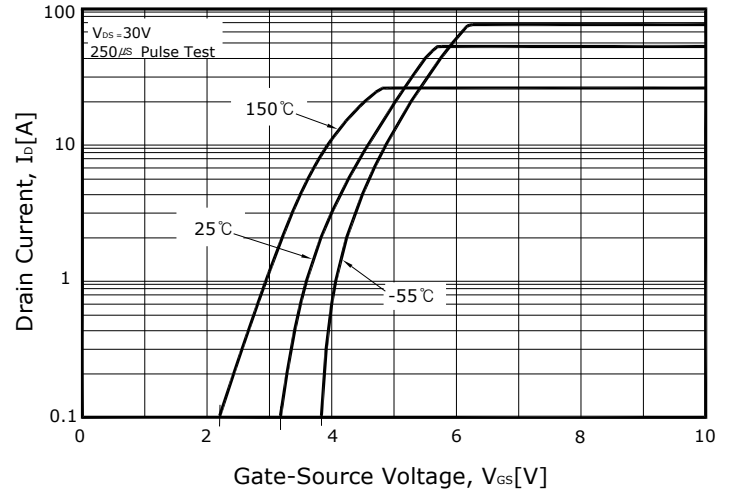


Fig. 3 $R_{DS(ON)} - I_D$

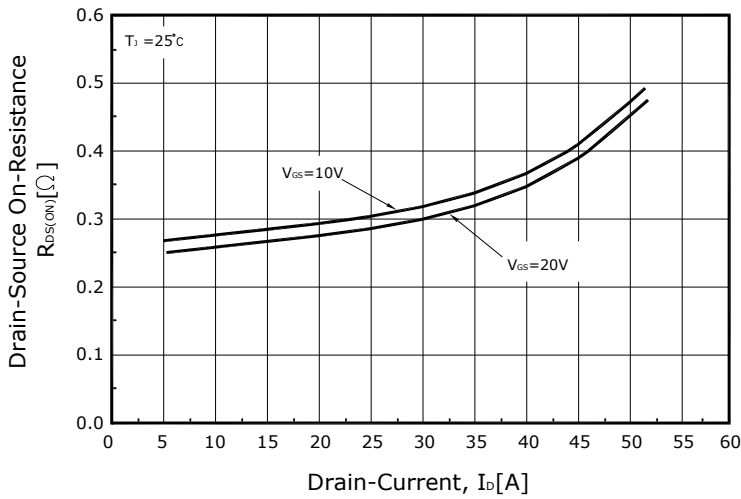


Fig. 4 $I_{DR} - V_{SD}$

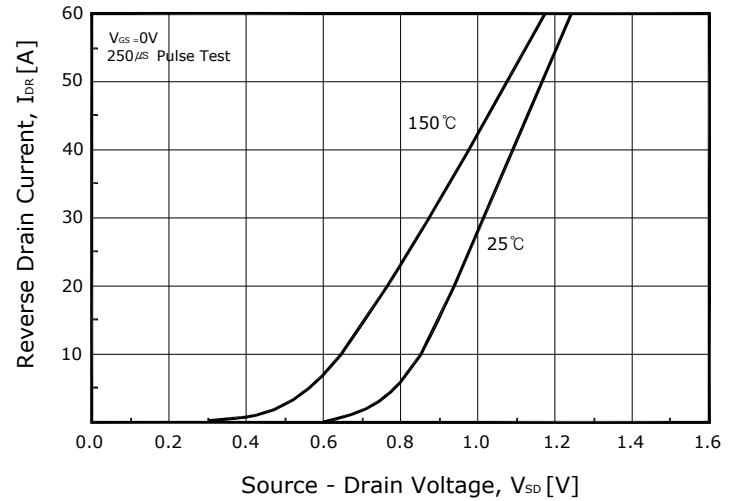


Fig. 5 Capacitance - V_{DS}

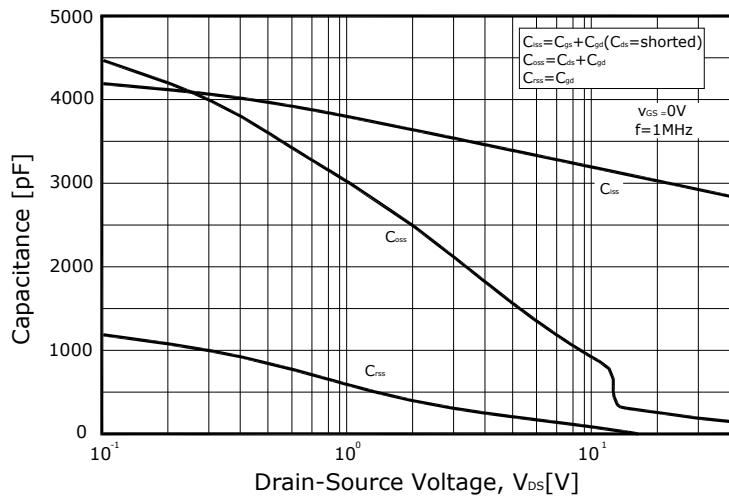
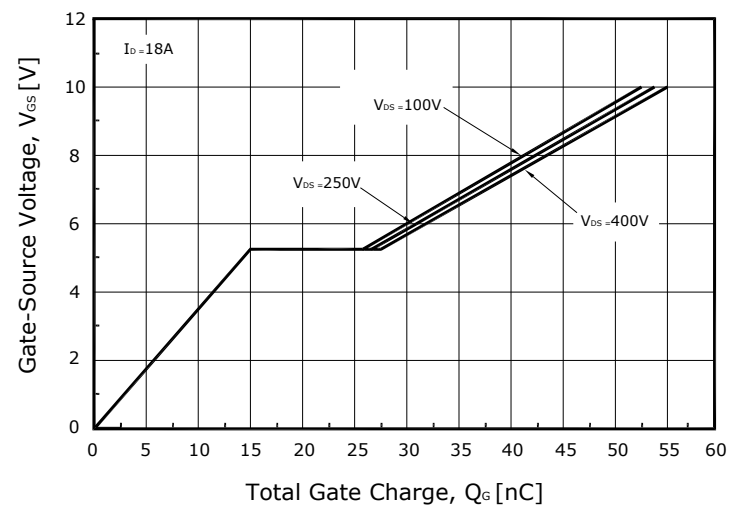


Fig. 6 $V_{GS} - Q_G$



Electrical Characteristics Curve (Continue)

Fig. 7 $BV_{DSS} - T_J$

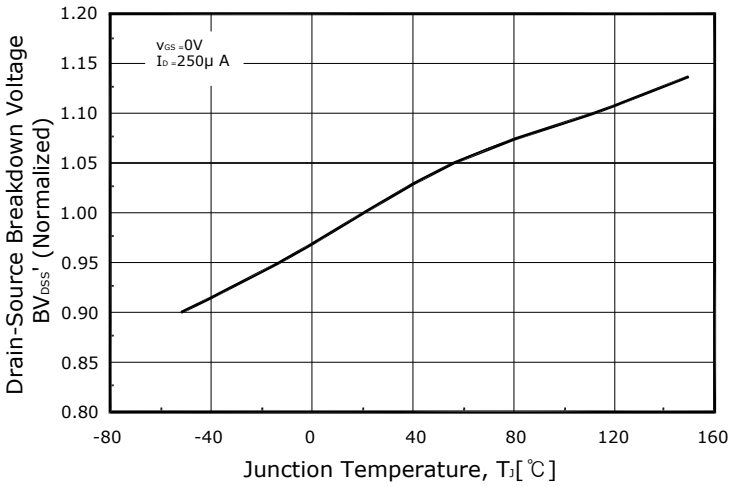


Fig. 8 $R_{DS(ON)} - T_J$

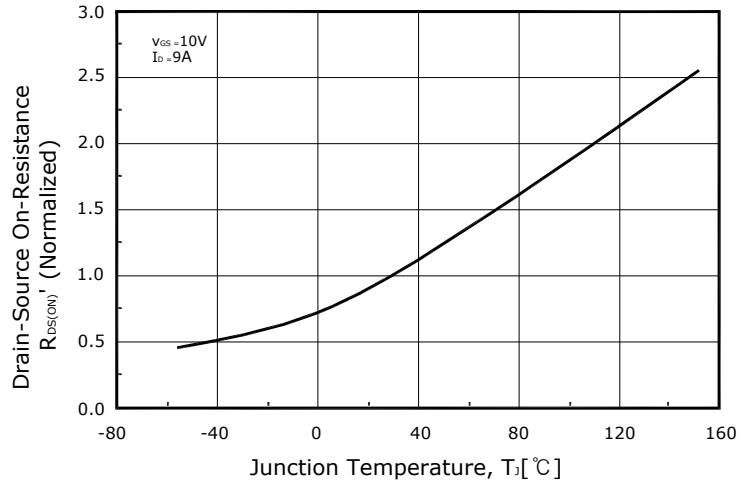


Fig. 9 $I_D - T_C$

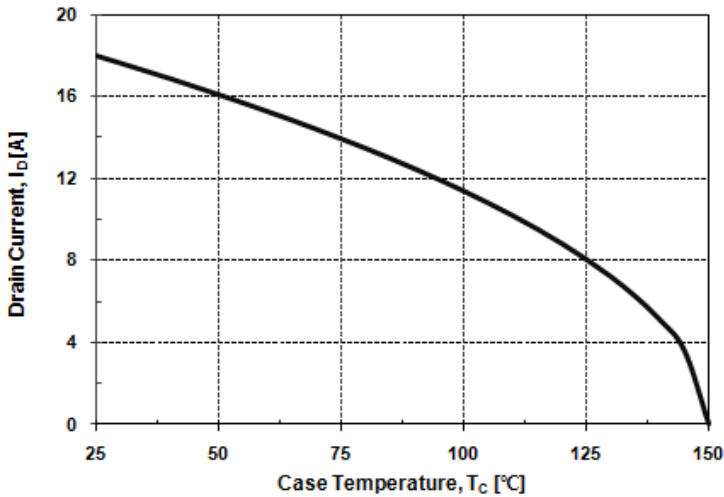


Fig. 10 Safe Operating Area

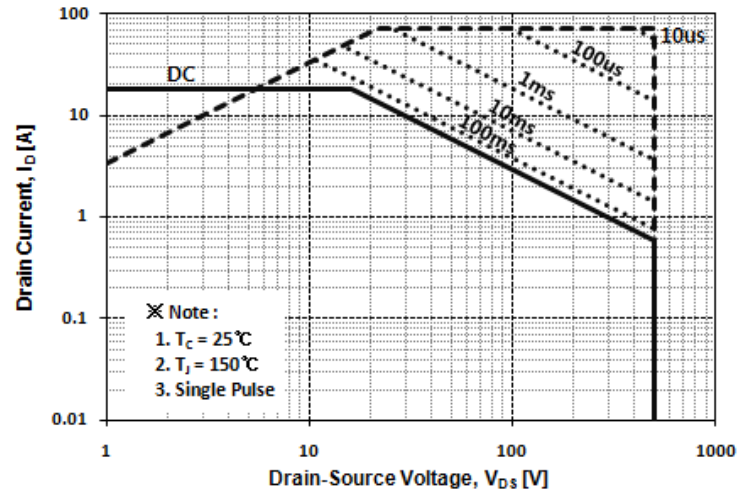


Fig. 11 Transient Thermal Impedance

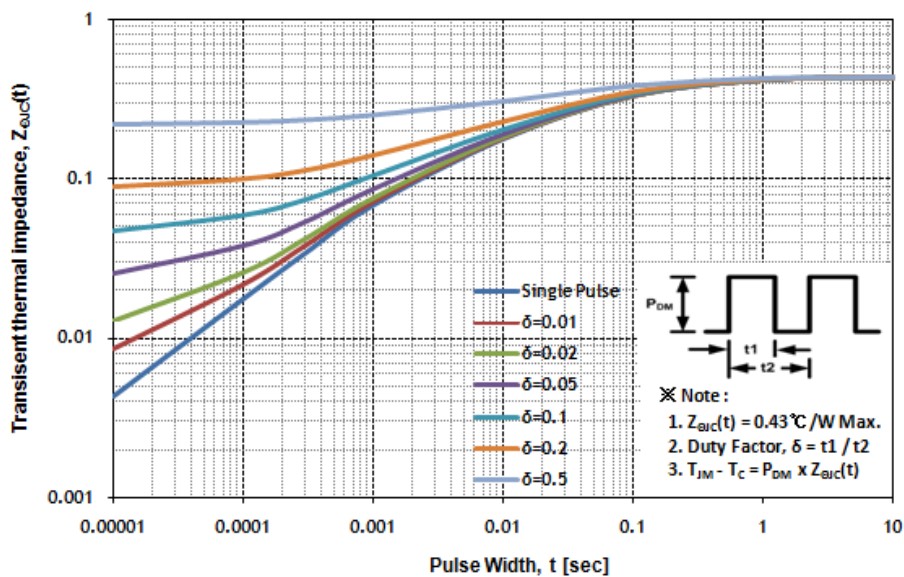


Fig. 12 Gate Charge Test Circuit & Waveform

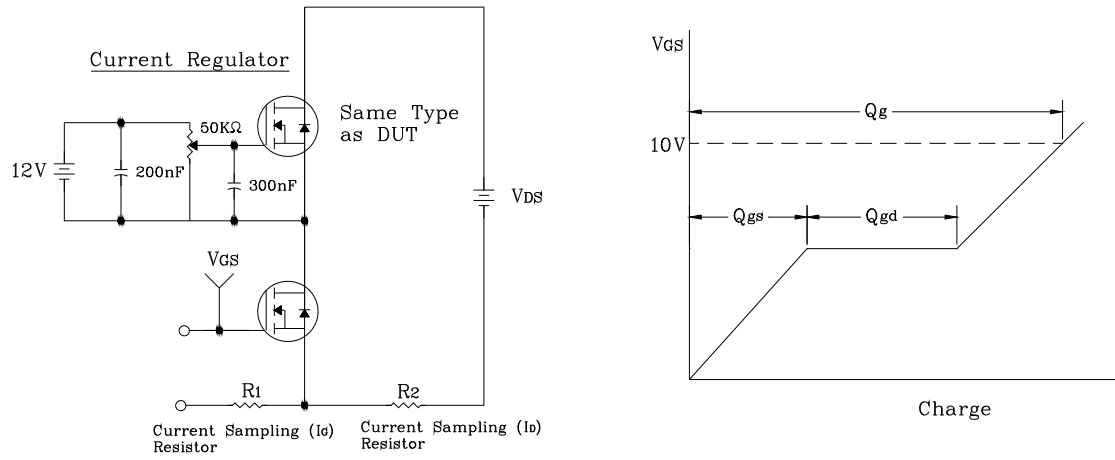


Fig. 13 Resistive Switching Test Circuit & Waveform

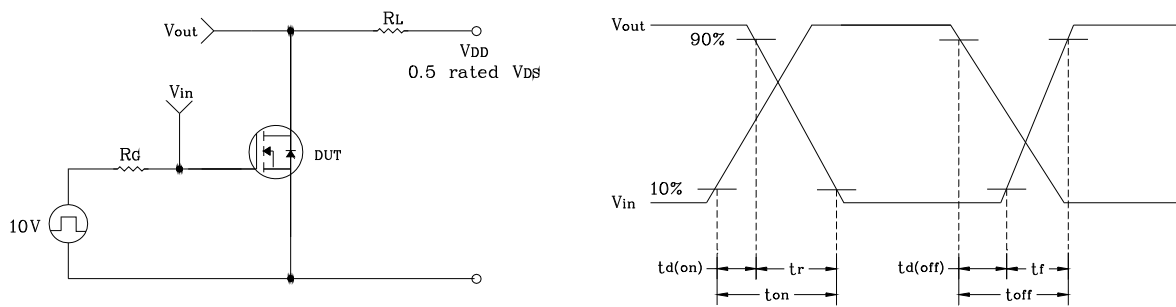


Fig. 14 E_{AS} Test Circuit & Waveform

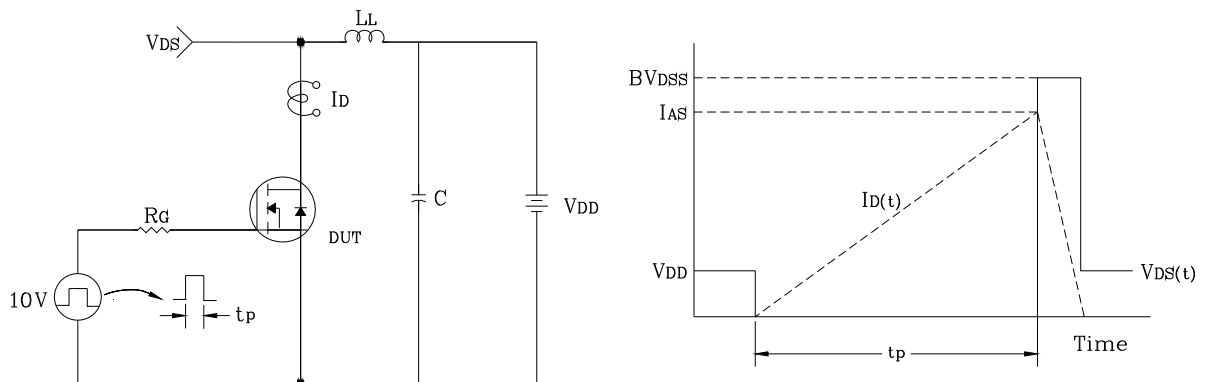
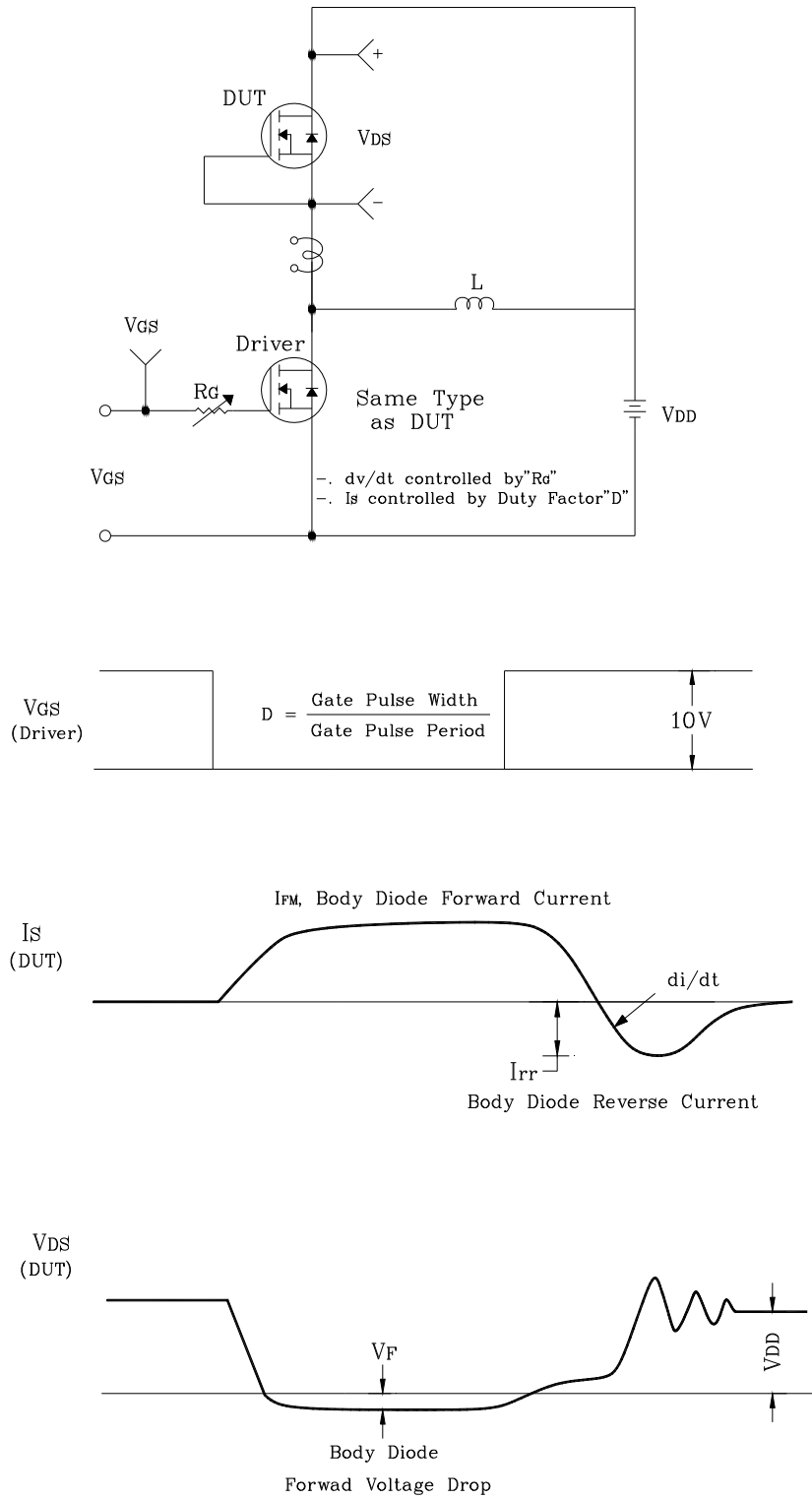
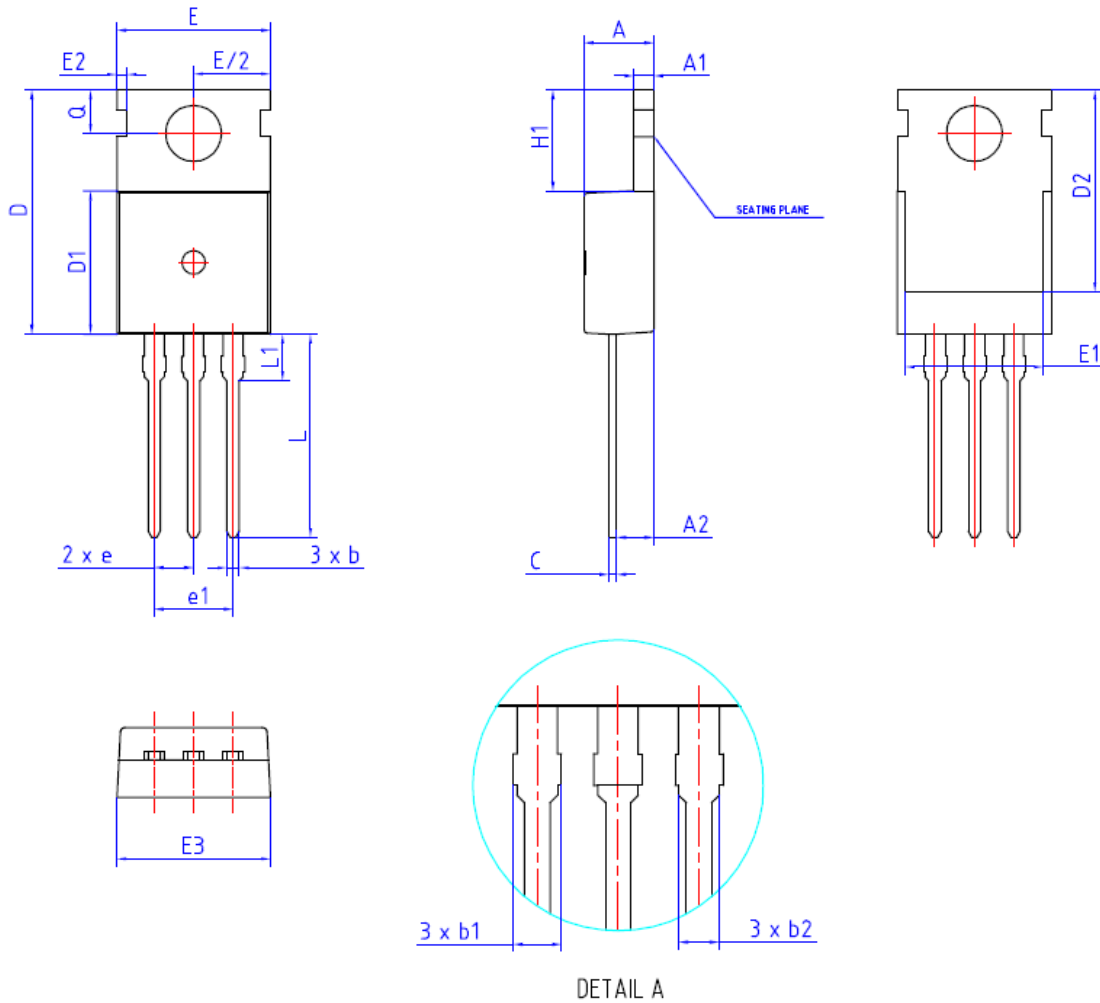


Fig. 15 Diode Reverse Recovery Time Test Circuit & Waveform



Package Outline Dimensions



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	4.30	4.50	4.70	
A1	1.25	1.30	1.40	
A2	2.20	2.40	2.60	
b	0.70	0.80	0.90	
b1	1.42	1.52	1.62	
b2	1.17	1.27	1.37	
C	0.45	0.50	0.60	
D	15.50	15.70	15.90	
D1	9.00	9.20	9.40	
D2	13.10	13.30	13.50	
E	9.70	9.90	10.10	
E1	-	-	8.90	
E2	(0.60 REF)			
E3	9.80	10.00	10.20	
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.50	6.70	
L	12.88	13.08	13.28	
L1	(3.00 REF)			
øP	3.40	3.60	3.80	
Q	2.70	2.80	2.90	

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